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THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	TYP.	MAX.	UNIT		
Maximum Junction-to-Ambient	R _{thJA}	-	62			
Case-to-Sink, Flat, Greased Surface	R _{thCS}	0.50	-	°C/W		
Maximum Junction-to-Case (Drain)	R _{thJC}	-	1.0			

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static		-			•	•		
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		200	-	-	V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Reference	to 25 °C, I _D = 1 mA	-	0.27	-	V/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V$	/ _{GS} , I _D = 250 μΑ	1.0	-	2.0	V	
Gate-Source Leakage	I _{GSS}	V	G _S = ± 10	-	-	± 100	nA	
Zene Oete Vielte en Durin Ouwant		V _{DS} = 200 V, V _{GS} = 0 V		-	-	25		
Zero Gate Voltage Drain Current	9 Gate Voltage Drain Current I_{DSS} $V_{DS} = 160 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 \text{ °C}$		-	-	250	μA		
Duraine Converse One Ottata Desciptance	R _{DS(on)}	V _{GS} = 5.0 V	I _D = 10 A ^b	-	-	0.18		
Drain-Source On-State Resistance		V _{GS} = 4.0 V	I _D = 8.5 A ^b	-	-	0.27	Ω	
Forward Transconductance	9 _{fs}	V _{DS} = 5	50 V, I _D = 10 A ^b	16	-	-	S	
Dynamic		• •			•	•		
Input Capacitance	C _{iss}	V	/ _{GS} = 0 V,	-	1800	-	pF	
Output Capacitance	C _{oss}	V	$T_{\rm DS} = 25 \rm V$	-	400	-		
Reverse Transfer Capacitance	C _{rss}	f = 1.0	f = 1.0 MHz, see fig. 5		120	-	1	
Total Gate Charge	Qg			-	-	66	nC	
Gate-Source Charge	Q _{gs}	V _{GS} = 5.0 V	$V_{GS} = 5.0 V$ $I_D = 17 A, V_{DS} = 160 V,$ see fig. 6 and 13 ^b		-	9.0		
Gate-Drain Charge	Q _{gd}		see lig. o and to	-	-	38	1	
Turn-On Delay Time	t _{d(on)}	V_{DD} = 100 V, I _D = 17 A R _g = 4.6 Ω, R _D = 5.7 Ω, see fig. 10 ^b		-	8.0	-	- ns	
Rise Time	t _r			-	83	-		
Turn-Off Delay Time	t _{d(off)}			-	44	-		
Fall Time	t _f			-	52	-		
Internal Drain Inductance	L _D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	– nH	
Internal Source Inductance	L _S			-	7.5	-		
Gate Input Resistance	Rg	f = 1 MHz, open drain		0.3	-	1.2	Ω	
Drain-Source Body Diode Characteristic	S	• •			•	•		
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	17	A	
Pulsed Diode Forward Current ^a	I _{SM}			-	-	68		
Body Diode Voltage	V _{SD}	$T_{\rm J}$ = 25 °C, $I_{\rm S}$ = 17 A, $V_{\rm GS}$ = 0 V ^b		-	-	2.0	V	
Body Diode Reverse Recovery Time	t _{rr}	T _ 05 °C			310	470	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	- T _J = 25 °C, I _F = 17 A, dl/dt = 100 A/µs ^b		-	3.2	4.8	μC	
Forward Turn-On Time	t _{on}	Intrinsic turn	on time is negligible (turn	-on is do	minated b	by L _S and	L _D)	

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width \leq 300 µs; duty cycle \leq 2 %.

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

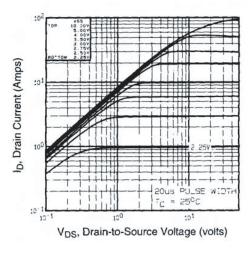


Fig. 1 - Typical Output Characteristics, $T_C = 25 \ ^{\circ}C$

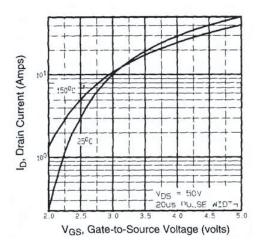


Fig. 3 - Typical Transfer Characteristics

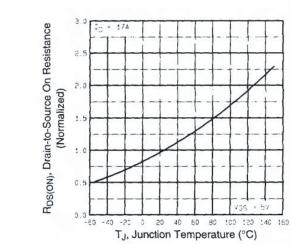


Fig. 4 - Normalized On-Resistance vs. Temperature

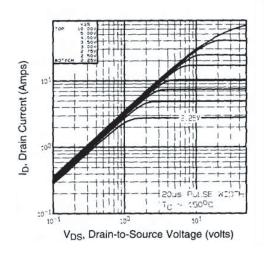
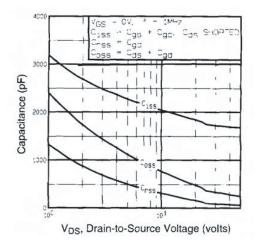


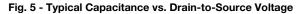
Fig. 2 - Typical Output Characteristics, T_C = 150 °C

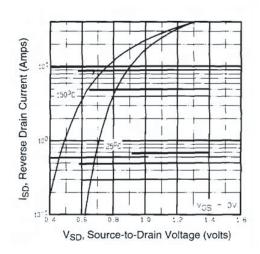


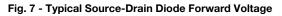
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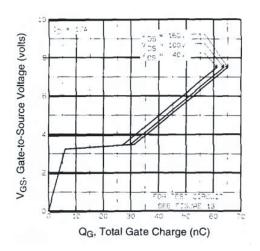


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

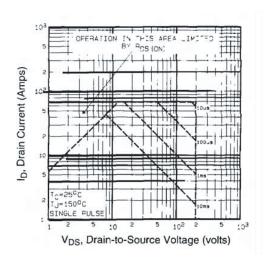


Fig. 8 - Maximum Safe Operating Area

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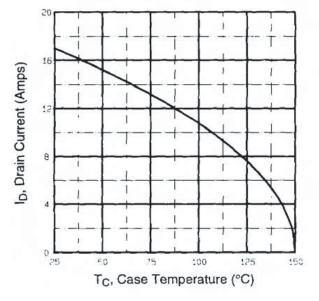


Fig. 9 - Maximum Drain Current vs. Case Temperature

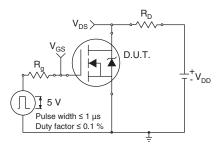


Fig. 10a - Switching Time Test Circuit

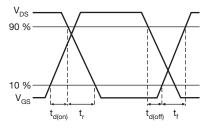
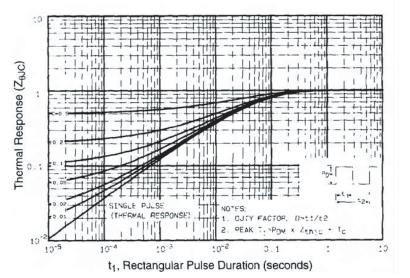


Fig. 10b - Switching Time Waveforms





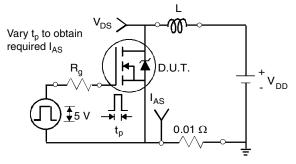


Fig. 12a - Unclamped Inductive Test Circuit

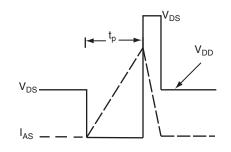


Fig. 12b - Unclamped Inductive Waveforms

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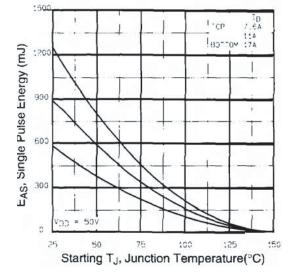


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

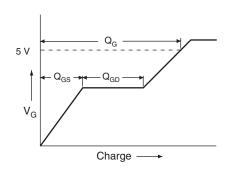


Fig. 13a - Basic Gate Charge Waveform

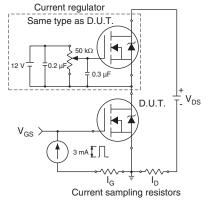
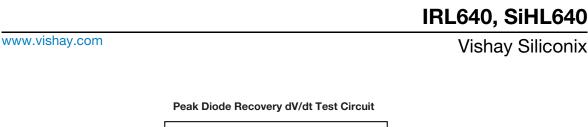
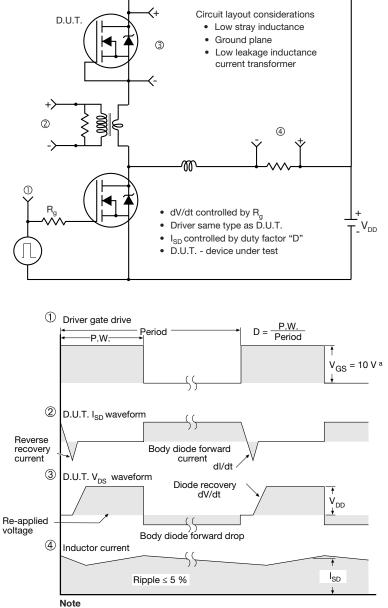


Fig. 13b - Gate Charge Test Circuit

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a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

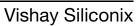
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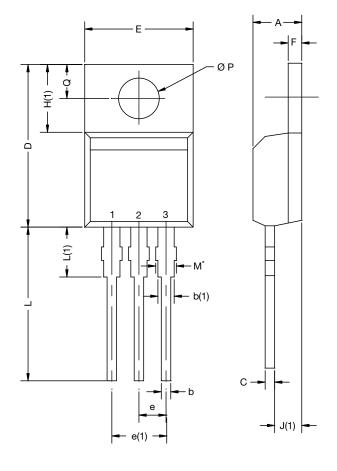
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TO-220-1



DIM.	MILLIN	IETERS	INCHES			
Dilvi.	MIN.	MAX.	MIN.	MAX.		
А	4.24	4.65	0.167	0.183		
b	0.69	1.02	0.027	0.040		
b(1)	1.14	1.78	0.045	0.070		
С	0.36	0.61	0.014	0.024		
D	14.33	15.85	0.564	0.624		
E	9.96	10.52	0.392	0.414		
е	2.41	2.67	0.095	0.105		
e(1)	4.88	5.28	0.192	0.208		
F	1.14	1.40	0.045	0.055		
H(1)	6.10	6.71	0.240	0.264		
J(1)	2.41	2.92	0.095	0.115		
L	13.36	14.40	0.526	0.567		
L(1)	3.33	4.04	0.131	0.159		
ØР	3.53	3.94	0.139	0.155		
Q	2.54	3.00	0.100	0.118		
ECN: X15-0364-Rev. C, 14-Dec-15 DWG: 6031						

Note

- M^{\star} = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM

Package Picture						
ASE		Xi'an				
EGNEOA 7KAB 193 Co A		IRF 9510 744K AB 25 (C) (A)				

Revison: 14-Dec-15

Document Number: 66542

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